



PTO/SB/08A (08-03)

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known	
		Application Number	10/763,018
		Filing Date	January 21, 2004
		First Named Inventor	Tan, Zhengquan
		Art Unit	2812
		Examiner Name	Unassigned
Sheet 1 of	Attorney Docket Number	016301-042210US	

U.S. PATENT DOCUMENTS+					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number Kind Code ² (if known)			
ML	AA	4,667,365	05-26-1987	Martinek	
	AB	4,690,746	09-01-1987	McInerney et al.	
	AC	4,737,379	04-12-1988	Hudgens et al.	
	AD	4,835,005	05-30-1989	Hirooka et al.	
	AE	4,890,575	01-02-1990	Ito et al.	
	AF	4,894,352	01-16-1990	Lane et al.	
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	AH	5,571,571	11-05-1996	Musaka et al.	
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	AN	5,750,211	05-12-1998	Weise et al.	
	AO	5,804,259	09-08-1998	Robles	
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	AQ	5,872,058	02-16-1999	Van Cleemput et al.	
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	AV	6,013,584	01-11-2000	M'Saad	
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	AY	6,039,851	03-21-2000	Iyer	
	AZ	6,051,321	04-18-2000	Lee et al.	
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	BC	6,150,212	11-21-2000	Divakaruni et al.	
	BD	6,150,285	11-21-2000	Besser et al.	
	BE	6,194,038	02-27-2001	Rossman	
ML	BF	6,194,038 B1	02-27-2001	Rossman	

Examiner Signature		Date Considered	10/7/04
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
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Examiner Name	Unassigned				
Sheet	2	of	Attorney Docket Number 016301-042210US		

U.S. PATENT DOCUMENTS+					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number Kind Code ² (if known)			
<i>ML</i>	BG	6,197,691	03-06-2001	Lee	
	BH	6,217,658 B1	04-17-2001	Orczyk et al.	
	BI	6,228,751 B1	05-08-2001	Yamazaki et al.	
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	BK	6,268,297 B1	07-31-2001	Nag et al.	
	BL	6,313,010 B1	11-06-2001	Nag et al.	
	BM	6,355,581 B1	03-12-2002	Vassiliev et al.	
<i>ML</i>	BN	6,395,150 B1	05-28-2002	Van Cleemput et al.	

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)				
<i>ML</i>	BO	EP	0 822 585	A2	02-04-1998	Applied Materials		<input type="checkbox"/>
<i>ML</i>	BP	JP	2-58836	A	02-28-1990			<input type="checkbox"/>
<i>ML</i>	BQ	JP	7-161703	A	06-23-1995			<input type="checkbox"/>
<i>ML</i>	BR	GB	2 267 291	A	12-01-1993			<input type="checkbox"/>
								<input type="checkbox"/>
								<input type="checkbox"/>

Examiner Signature	<i>[Signature]</i>	Date Considered	10/7/04
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Substitute for form 1449B/PTO			Complete if Known		
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			Art Unit	2812	
			Examiner Name	Unassigned	
Sheet	3	of		Attorney Docket Number	016301-042210US

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
<i>MSL</i>	BS	V.Y. Vassiliev et al., "Trends in Void Free Pre-metal CVD Dielectrics," <i>Solid State Technology</i> , pp. 129-136 (March 2001).		
	BT	L.Q. Qian et al., "High Density Plasma Deposition and Deep Submicron Gap Fill with Low Dielectric Constant SiOF Films," <i>February 21-22, 1995 DUMIC Conference</i> , pp. 50-56 (February 1995).		
	BU	T. Fukada et al., "Preparation of SiOF with Low Dielectric Constant by ECR Plasma CVD," <i>February 21-22, 1995 DUMIC Conference</i> , pp. 43-49 (February 1995).		
	BV	D. Yu et al., "Step Coverage Study of PETEOS Deposition for Intermetal Dielectric Applications," <i>June 12-13, 1990 VMIC Conference</i> , pp. 166-172 (June 1990).		
	BW	K. Musaka et al., "Single Step Gap Filling Technology for Subhalf Micron Metal Spacings on Plasma Enhanced TEOS/O ₂ Chemical Vapor Deposition System," <i>Extended Abstracts of the 1993 International Conference on Solid State Devices and Materials, Makuhari</i> , pp. 510-512 (1993).		
	BX	T. Fukuda et al., "Highly Reliable SiOF Film Formation Using High Density Plasma Containing Hydrogen," <i>February 10-11, 1997 DUMIC Conference</i> , pp. 41-49 (February 1997).		
	BY	G.Y. LEE et al., "A Low Redeposition Rate High Density Plasma CVD Process for High Aspect Ratio 175 nm Technology and Beyond," <i>Proceedings of IEEE 1999 International Interconnect Technology Conference</i> , pp. 152-154 (1999).		
	BZ	V.Y. Vassiliev et al., "Properties and Gap-Fill Capability of HDP-CVD Phosphosilicate Glass Films for Subquarter-Micrometer ULSI Device Technology," <i>Electrochemical and Solid-State Letters</i> , vol. 3, no. 2, pp. 80-83 (2000).		
	CA	NALWA, H.S., <i>Handbook of Low and High Dielectric Constant Materials and Their Applications</i> , vol. 1, page 66 (1999).		
<i>MSL</i>	CB	NGUYEN, s.v., "High-Density Plasma Chemical Vapor Deposition of Silicon-Based Dielectric Films for Integrated Circuits," <i>Journal of Research and Development</i> , vol. 43, 1/2 (1999).		

Examiner Signature	<i>Michael Lebowitz</i>	Date Considered	10/7/04
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